

Program of Session P

New Methods and Techniques for Crystal Growth

P1: August 6 (Wednesday), 9:00-10:00

Room: 207

Chair: Christiane Frank-Rotsch

9:00-9:30	P01 (Invited) Thermophysical Properties and Rapid Solidification of Refractory Alloys aboard the China Space Station Haipeng Wang, Hui Liao, Liang Hu, Bingbo Wei, Northwestern Polytechnical University, CHINA
09:30 – 09:45	P02 (Oral) Micro-XRF for assessing structural crystal quality: bulk crystal growth of Sr ₂ DyNbO ₆ Christian Hirschle¹, Christo Gugushev², Darrell Schlom², Roald Tagle¹, 1. Bruker Nano GmbH, 2. Leibniz-Institut für Kristallzüchtung, GERMANY
09:45 – 10:00	P03 (Oral) X-ray topography by means of laboratory scale micro-XRF devices Christo Gugushev¹, Christian Hirschle², Kaspars Dadzis¹, Albert Kwasniewski¹, Michael Schulze¹, Leonard Schellkopf², Carsten Richter¹, 1. Leibniz-Institut für Kristallzüchtung, 2. Bruker Nano GmbH, GERMANY

P2: August 6 (Wednesday), 11:00-12:00

Room: 207

Chair: Shigeo Naritsuka

11:00 – 11:30	P04 (Invited) In-situ visualization of crystallization interface in vertical Bridgman growth of fluoride crystals Zhonghan Zhang, Liangbi Su, Shanghai Institute of Ceramics, CAS, CHINA
11:30-- 11:45	P05 (Oral) Crystal Casting Method Enabled by Iodine Doping and Melt-Aging Procedures Shohei Kodama, Shogo Omiya, Gaito Shimura, Ikuo Yanase, Hiroaki Takeda, Saitama University, JAPAN
11:45-- 12:00	P06 (Oral) Crystal orientation quantification in 10 seconds Plex Lee, Dirk Kok, Malvern Panalytical, CHINA

P3: August 7 (Thursday), 11:00-12:15

Room: 207

Chair: Rukang Li

11:00-11:30	P07 (Invited) Growth of ~15 μ m Diameter Ultra-fine Single Crystal Fiber by LHPG for Extreme Environment Sensor Application Zhitai Jia, State Key Laboratory of Crystal Materials, Shandong University, CHINA
11:30-12:00	P08 (Invited) Modern application of travelling magnet fields for semiconductor materials Christiane Frank-Rotsch, Natasha Dropka, Uta Juda, Oleg Root, Lenka Smejkalova, Gagan Kumar Chappa, Frank Michael Kießling, Leibniz-Institut für Kristallzüchtung (IKZ), GERMANY
12:00-12:15	P09 (Oral) GaAs nanochannel epitaxy on Si substrate using patterned graphene as a mask Shigeya Naritsuka, Ayaka Osumi, Wataru Ohta, Takahiro Maruyama, Meijo University, JAPAN

P4: August 7 (Thursday), 14:00-14:45

Room: 207

Chair: Anhua Wu

14:00-14:30	P10 (Invited) Research on the Growth and Microstructure of InSe Semiconductor Crystal on China Space Station Min Jin, Shanghai Dianji University, CHINA
14:30-14:45	P11 (Oral) Crystal growth and optical properties of KBe ₂ BO ₃ F ₂ by horizontal Bridgman method Tianhong Huang, Tong Wu, Shuangyue Shang, Lijuan Liu, Xiaoyang Wang, Technical Institute of Physics and Chemistry CAS, CHINA